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--25. (New) The method of transferring a three-dimensional device according to claim 21, the at least one thin film device layer being deposited by transferring being formed simultaneously with at least one other of the thin film device layers.--

REMARKS

Claims 1-25 are pending. Claims 11 and 15-20 have previously been withdrawn from consideration. By this Amendment, claims 1-3 are amended and claims 21-25 are added. Reconsideration based on the following remarks is respectfully requested.

The attached Appendix includes marked-up copies of each amended claim (37 C.F.R. §1.121(c)(1)(ii)).

I. The Claims Define Patentable Subject Matter

The Office Action rejects claims 1-9 and 12-14 under 35 U.S.C. §102(a) over Zavracky et al. (U.S. Patent No. 5,656,548), and claim 10 under 35 U.S.C. §103(a) over Zavracky et al. in view of Yoshizawa et al. (U.S. Patent No. 5,819,406). These rejections are respectfully traversed.

Zavracky et al. does not disclose a three-dimensional device in which, inter alia, at least one thin film device layer is deposited by a transfer method including a separation in a separable layer on which the at least one thin film device layer is formed, as recited in claim 1, and as similarly recited in claims 2 and 21.

Instead, Zavracky et al. discloses a multi-layered microprocessor fabricated upon a first layer 200 and a second layer 100. However, neither layer 100 nor layer 200 is deposited by a transfer method including a separation in a separable layer. The components of the multi-layer microprocessor of Zavracky et al. are fabricated directly on to the first layer 200 and the second layer 100. See, for example, Fig. 10 of Zavracky et al.

Providing a three-dimensional device in which at least one thin film device layer is deposited by a transfer method including a separation in a separable layer on which the at

least one thin film device layer is formed provides significant advantages. For example, depositing at least one thin film device layer by a transfer method allows the use of a substrate that has a glass transition point less than the maximum temperature required during the formation of the thin film device layers. See, for example, page 19, lines 6-11 of the specification.

Zavracky et al. does not disclose the three-dimensional device of claim 1 or claim 2, or the method of claim 21. Yoshizawa et al. does not make up for the deficiencies of Zavracky et al. Thus, combining Yoshizawa et al. with Zavracky et al. would not result in the claimed invention.

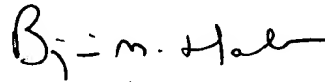
For at least these reasons, it is respectfully submitted that claims 1, 2 and 21 are patentable over the applied references. The dependent claims are likewise patentable over the applied references for at least the reasons discussed as well as for the additional features they recite. Applicants respectfully request that the rejections under 35 U.S.C. §102 and §103 be withdrawn.

II. Conclusion

In view of the foregoing, Applicants respectfully submit that this application is in condition for allowance. Favorable consideration and prompt allowance are earnestly solicited.

Should the Examiner believe anything further is desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,



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Attachments:

Appendix
Amendment Transmittal
Petition for Extension of Time

Date: November 29, 2001

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<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
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APPENDIX

Changes to Claims:

The following is a marked-up version of the amended claim:

1. (Twice Amended) A three-dimensional device comprising:
a plurality of thin film device layers deposited in a thickness direction, each thin film device layer being disposed in a predetermined region in a planar direction, at least one of the thin film device layers being deposited by a transfer method including a separation in a separable layer on which the at least one thin film device layer is formed.
2. (Twice Amended) A three-dimensional device comprising:
a plurality of thin film device layers deposited on a base in a thickness direction for constituting a three-dimensional circuit, each thin film device layer constituting a circuit disposed in a predetermined region extending in a planar direction, at least one of the thin film device layers being deposited by a transfer method including a separation in a separable layer on which the at least one thin film device layer is formed.
3. (Twice Amended) The three-dimensional device according to claim 1, further comprising a first substrate, the transfer method comprising forming the at least one thin film device layer on a second substrate with athe separable layer therebetween, and irradiating the separable layer with light to cause a separation in at least one of the separable layer and at an interface so that the at least one thin film device layer on the second substrate is transferred to the first substrate of the three-dimensional device.

Claims 21-25 are added.

- 21. (New) A method of transferring a three-dimensional device having a plurality of thin film device layers to a first substrate, comprising:
forming at least one thin film device layer on a second substrate with a separable layer therebetween; and

irradiating the separable layer with light to cause a separation in at least one of the separable layers and at an interface so that the at least one thin film device layer on the second substrate is transferred to the first substrate.--

--22. (New) The method of transferring a three-dimensional device according to claim 21, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.--

--23. (New) The method of transferring a three-dimensional device according to claim 21, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.--

--24. (New) The method of transferring a three-dimensional device according to claim 21, the light being a laser beam.--

--25. (New) The method of transferring a three-dimensional device according to claim 21, the at least one thin film device layer being deposited by transferring being formed simultaneously with at least one other of the thin film device layers.--